

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE CLAIMS**

1. (Amended) A contact comprising:  
a conductive film;  
an opening **formed through a plurality of film stacks, said opening** having a top and bottom wherein said bottom is formed on said conductive film, said opening having a first sidewall and second sidewall wherein said first sidewall is opposite of said second sidewall, and wherein said first sidewall has a stair step configuration wherein said first sidewall is closer to said second sidewall at said bottom of said opening [**then**] **than** at the top of said opening; and  
a **continuous** conductor formed on **said stair step configuration** said first sidewall of said opening and on said bottom of said opening on said conductive film.

3. (Amended) The contact of claim 1 wherein said **continuous** conductor is aluminum or aluminum alloy.

4. (Amended) The contact of claim 1 wherein said first sidewall has a slope of less than [**2-1**] **2:1**.

5. (Amended) A contact comprising:  
a contact opening having a bottom on [**a**] **an** interconnection, said contact opening having a first and second laterally opposite sidewalls, wherein said first sidewall comprises:  
a first vertical side extending up from said bottom;

a first horizontal surface extending from said first vertical side to a second vertical side, said second vertical side further spaced from said second sidewall than said first vertical side;

a second horizontal surface extending from said second vertical side to a third vertical side wherein said third vertical side is spaced further from said second sidewall than said second vertical side; and

a **continuous** conductor formed on said first sidewall and on said interconnection in the bottom of said contact opening.

6. (Amended) The contact of claim [1] 5 wherein said conductor is an aluminum or an aluminum alloy.

**Please add new claims:**

26. (New) The contact of claim 13 wherein said silicide film comprises titanium silicide.

27. (New) The contact of claim 14 wherein said silicide film comprises titanium silicide.

28. (New) The contact of claim 5 wherein said continuous conductor comprises a top p+ silicon film formed on a silicide film.

29. (New) The contact of claim 28 wherein said silicide film comprises titanium silicide.

30. (New) The contact of claim 5 wherein said continuous conductor comprises a top n+ silicon film formed on a silicide film.

31. (New) The contact of claim 30 wherein the silicide film comprises titanium silicide.